P-channel Enhancement Mode Power MOSFET

Features

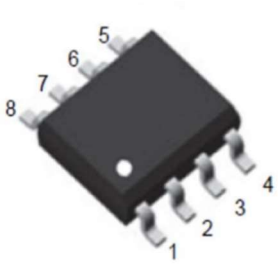
- VDS= -150V, ID= -2.8A
  RDS(ON) < 160mΩ @ VGS = -10V
  RDS(ON) < 200mΩ @ VGS = -4.5V

General Features

- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead Free and Green Available

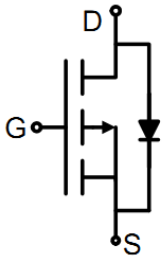
100% UIS TESTED!
100% ΔVds TESTED!

RoHS



SOP-8

pin assignment



Schematic diagram

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 150	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 2.8	A
	T_C = 70 °C		- 2.3	
	T_A = 25 °C		- 2[a, b]	
	T_A = 70 °C		- 1.6[a, b]	
Pulsed Drain Current		I_{DM}	- 15	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 4.9	
	T_A = 25 °C		- 2.5[a, b]	
Avalanche Current	L = 0.1 mH	I_{AS}	- 15	
Single-Pulse Avalanche Energy		E_{AS}	11.25	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	5.9	W
	T_C = 70 °C		3.8	
	T_A = 25 °C		3.1[a, b]	
	T_A = 70 °C		2[a, b]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. t = 10 s.
c. Based on T_C = 25 °C.

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[a, b]	t ≤ 10 s	R_{thJA}	33	40	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21	

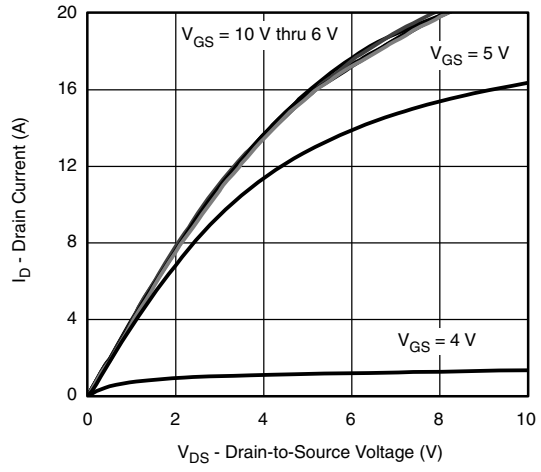
Notes:
a. Surface mounted on 1" x 1" FR4 board.
b. Maximum under steady state conditions is 80 °C/W.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 150			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 165		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 2		- 4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 150 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 150 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ - 5 V, V_{GS} = - 10 V	- 8			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 2 A		0.160		Ω
		V_{GS} = - 4.5V, I_D = - 1.5 A		0.200		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = 2 A		12		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 50 V, V_{GS} = 0 V, f = 1 MHz		1190		pF
Output Capacitance	C_{oss}			61		
Reverse Transfer Capacitance	C_{rss}			42		
Total Gate Charge	Q_g	V_{DS} = - 75 V, V_{GS} = - 10 V, I_D = - 2 A		27.5	42	nC
		V_{DS} = - 75 V, V_{GS} = - 6 V, I_D = - 2 A		23.2	35	
Gate-Source Charge	Q_{gs}			5.4		
Gate-Drain Charge	Q_{gd}			8.4		
Gate Resistance	R_g	f = 1 MHz		6.1	9.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 75 V, R_L = 25 Ω, $I_D \cong$ - 3 A, V_{GEN} = - 6 V, R_g = 1 Ω		20	30	ns
Rise Time	t_r			95	145	
Turn-Off DelayTime	$t_{d(off)}$			38	60	
Fall Time	t_f			34	51	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 75 V, R_L = 25 Ω, $I_D \cong$ - 2 A, V_{GEN} = - 10 V, R_g = 1 Ω		11	18	
Rise Time	t_r			28	42	
Turn-Off DelayTime	$t_{d(off)}$			52	78	
Fall Time	t_f			35	53	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 13	A
Pulse Diode Forward Current[a]	I_{SM}				- 15	
Body Diode Voltage	V_{SD}	I_S = - 2 A		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 4 A, dI/dt = 100 A/µs, T_J = 25 °C		65	90	ns
Body Diode Reverse Recovery Charge	Q_{rr}			180	270	nC
Reverse Recovery Fall Time	t_a			45		ns
Reverse Recovery Rise Time	t_b			20		

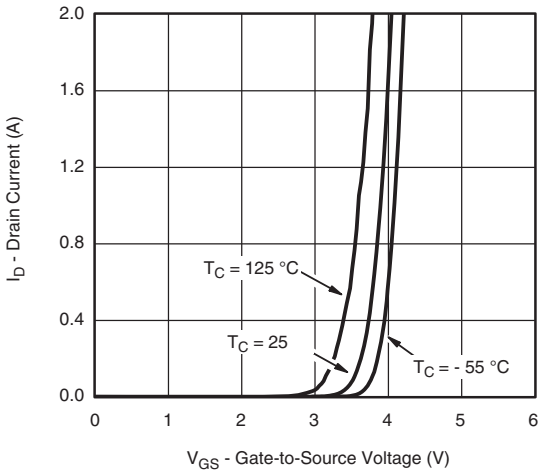
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

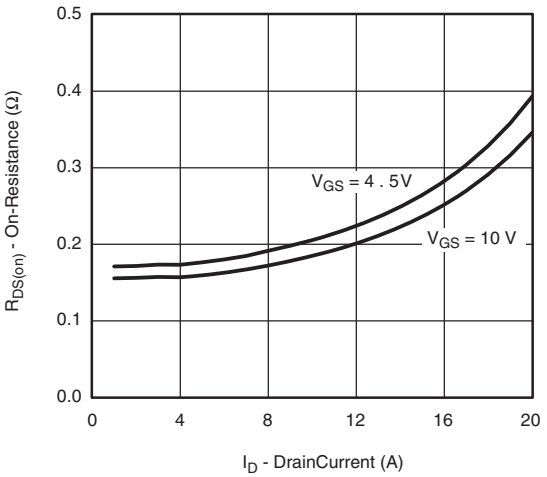
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



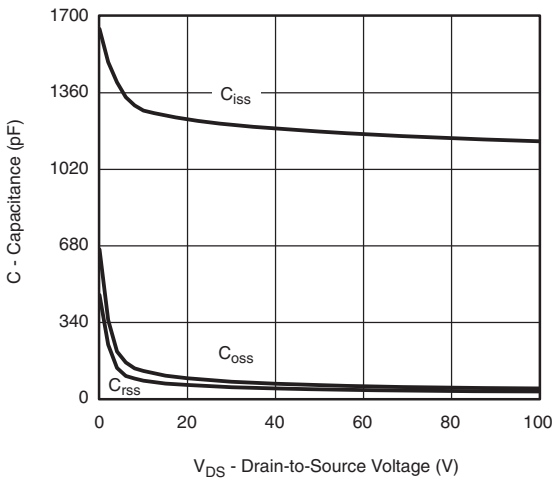
Output Characteristics



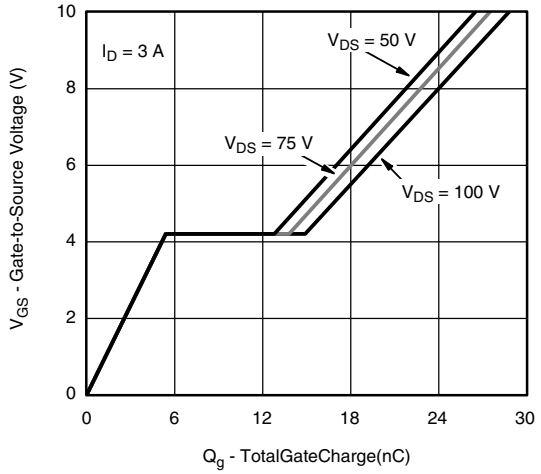
Transfer Characteristics



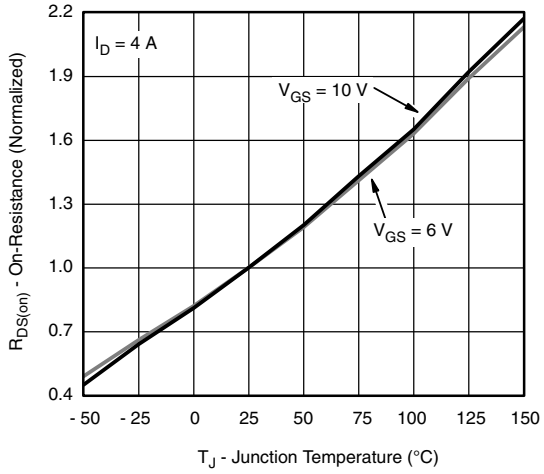
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

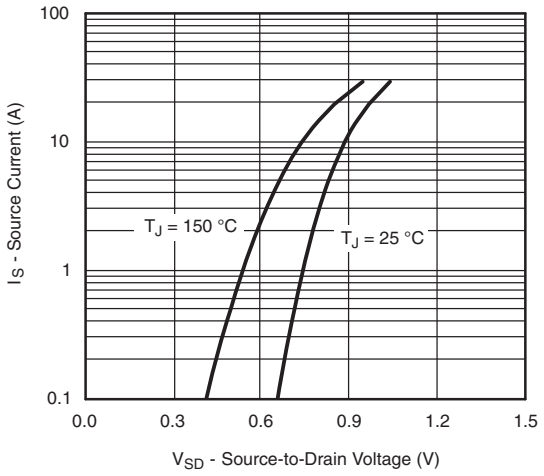


Gate Charge

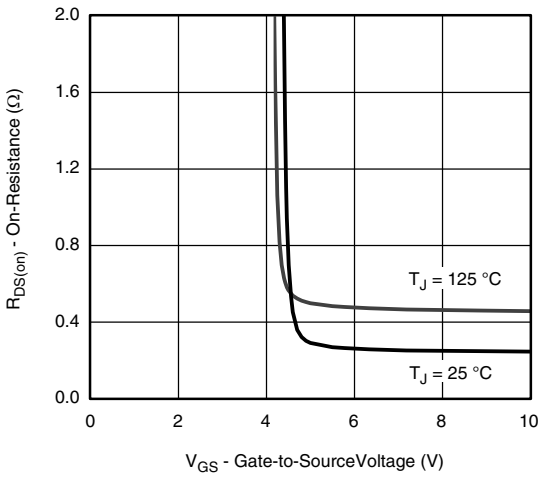


On-Resistance vs. Junction Temperature

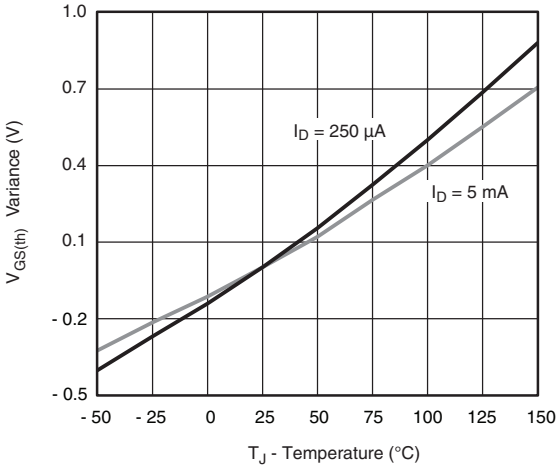
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



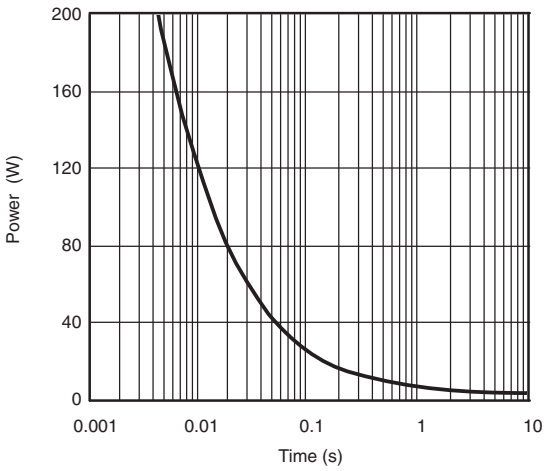
Source-Drain Diode Forward Voltage



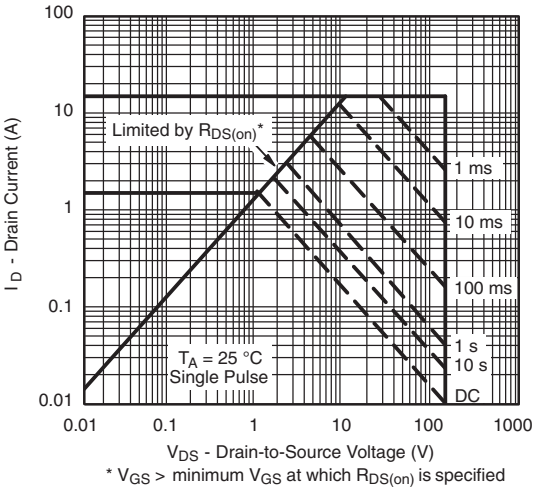
On-Resistance vs. Gate-to-Source Voltage



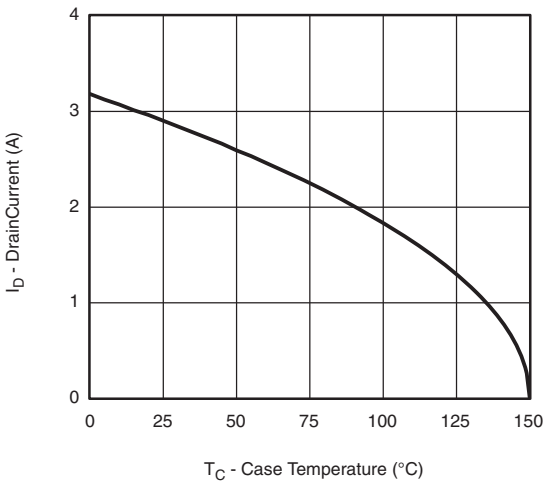
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

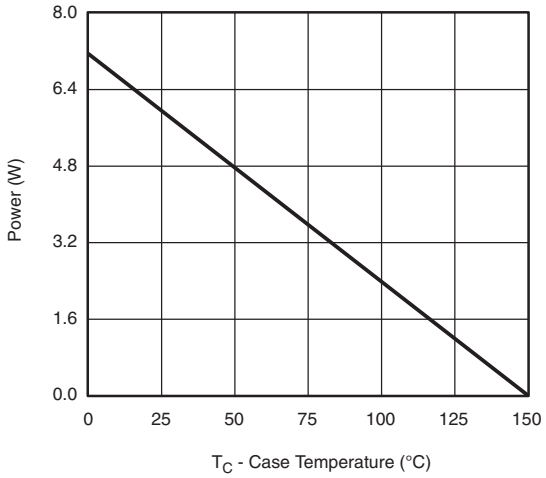


Safe Operating Area, Junction-to-Ambient

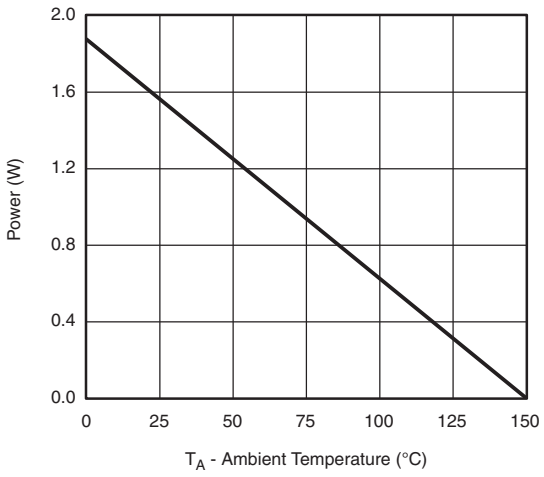


Current Derating*

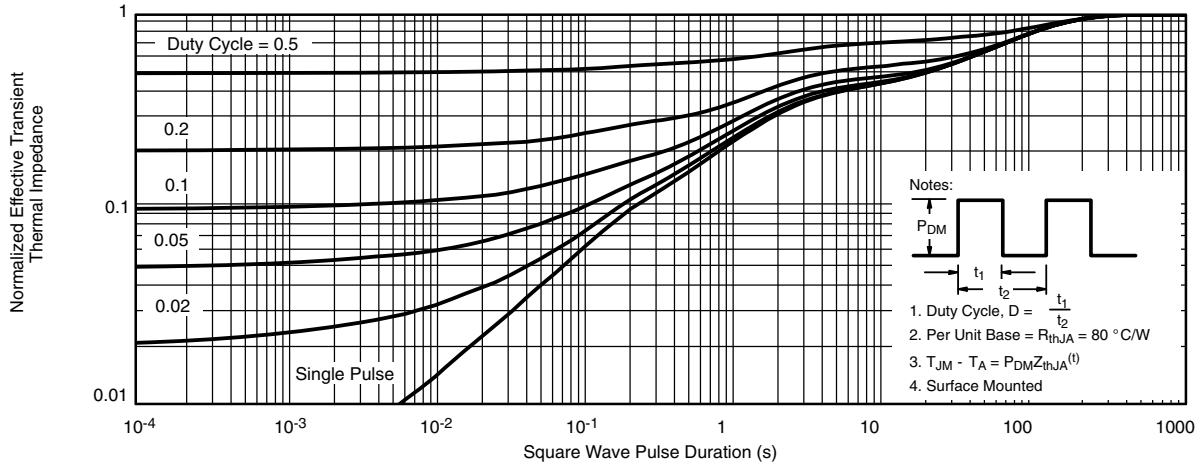
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



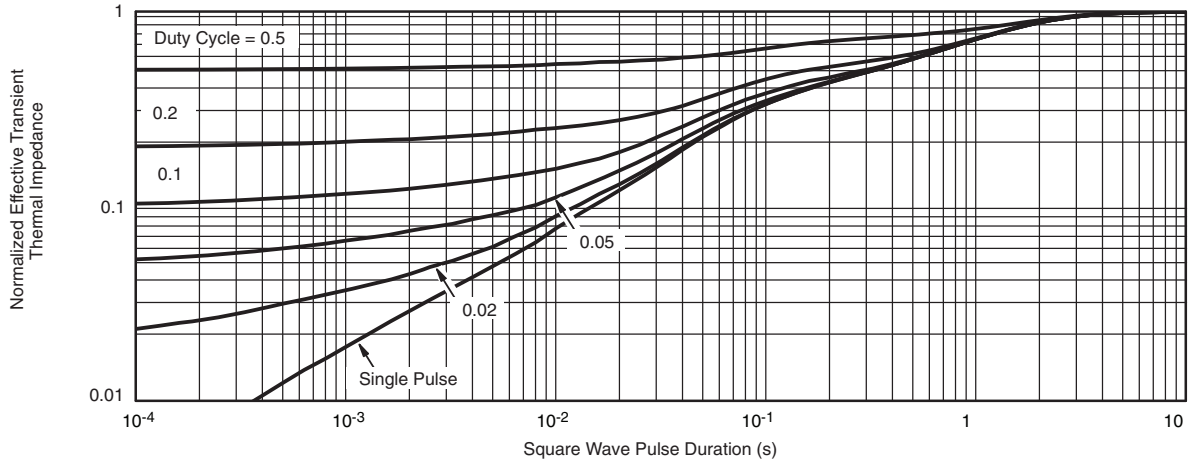
Power, Junction-to-Foot



Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot